



**0.5- $\mu\text{m}$  2MI Process Cross Section**

## General Description

The 0.5- $\mu\text{m}$  Low-Noise, Low-Current MesFET (LNLC) process is a cost-effective 2MI (2-metal-interconnect) depletion-mode ion-implant MesFET process for low-noise applications through 20 GHz. The LNLC process allows for switch, amplifier and diode integration and is used mainly in low-noise amplifier applications such as receivers. Passives include 2 thick-metal interconnect layers, precision TaN resistors, GaAs resistors, MIM capacitors, and through-substrate vias. The via-under-cap process aids in size compaction and offers excellent grounds at higher frequencies.

## Features

- 0.5- $\mu\text{m}$  amplifier transistors
- 0.5- $\mu\text{m}$  switch transistors
- 0.5- $\mu\text{m}$  diodes
- Device passivation
- High-Q passives
- MIM capacitors
- TaN resistors
- GaAs resistors
- 2 metal layers
- Air bridges
- Substrate vias
- Operation up to  $V_d = 5\text{ V}$

## Applications

- Up to 20 GHz
- Communications
- Space
- Military
- Low-noise amplifiers
- Driver amplifiers
- AGC amplifiers
- Limiting amplifiers
- Transimpedance amplifiers
- Differential amplifiers
- Digital and analog phase shifters
- Digital and analog attenuators
- Mixers (up and down converters)
- Multipliers
- Switches
- Oscillators

0.5- $\mu\text{m}$ Low-Noise MesFET Process Details			
Element	Parameter	Typical Value	Units
FETs	$I_{dss}$	190	mA/mm
	$G_m$	240	mS/mm
	$V_{bd}$	-13	V
	$V_p$	-1.15	V
MIM capacitors	density	300	pF/mm <sup>2</sup>
Capacitors over vias		yes	
TaN resistors	sheet resistance	50	$\Omega/\text{sq}$
GaAs resistors	sheet resistance	370	$\Omega/\text{sq}$
Vias		yes	
Substrate	thickness	100	$\mu\text{m}$

FET Models Available (Noise)		
Gate Pitch ( $\mu\text{m}$ )	Gate Fingers	FET Sizes ( $\mu\text{m}$ )
26 26	4	300
26 26	8	300

## Application Examples

### DC to 14 GHz Power Amplifier TGA8349-SCC:

The TriQuint TGA8349-SCC is a GaAs monolithic low-noise distributed amplifier designed for use as a multi-octave general-purpose gain block. The device provides 3.1 dB noise figure at mid-band. Typical power output is 16 dBm at 1-dB gain compression.

### 2 to 20 GHz Low-Noise Amplifier TGA8310-SCC:

The TriQuint TGA8310-SCC is a monolithic low-noise distributed amplifier, which operates from 2 to 20 GHz. Typically, noise figure is 4 dB with a small signal gain of 9 dB. This low-noise distributed amplifier is suitable for a variety of wideband electronic warfare systems such as radar warning receivers, electronic counter measures, decoys, jammers and phased array systems.

### Prototyping and Development

- Prototype Wafer Option (PWO)
  - Customer-specific masks
  - Customer schedule
  - 2 wafers delivered
  - Backside via process included
  - PCM (process control monitor) qualified wafers

### Design Tools

- Device libraries of circuit elements:
  - FETs
  - Thin-film and implanted resistors
  - Capacitors
  - Inductors
- Agilent ADS design kit
- MASC Library

### Training

- GaAs design classes:
  - Half-day introduction upon request
  - 3-day technical training upon request at the TriQuint Texas facility

### Process Status

0.5- $\mu$ m Low-Noise, Low-Current MesFET (LNLC) is fully released and qualified  
Contact TriQuint or visit  
<http://www.triquint.com/company/quality/>  
for more information on quality and reliability.

### Applications Services

- Tiling of GDSII stream files including PCM (process control monitor)
- Design rule checking
- Layout versus schematic checking
- Engineering:
  - On-wafer DC test
  - On-wafer RF test
  - Thermal analysis
  - Yield enhancement
- Part qualification
- Failure analysis
- Space qualification

### Manufacturing Services

- Mask making
- Wafer thinning
- Wafer dicing
- Substrate vias
- DC die-sort testing
- RF die-sort testing
- Final visual inspection